

Debre Tabor University Gafat Institute of Technology Department of Electrical and Computer Engineering				
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Course Code	ECEg4103			
Course Title	VLSI Design			
Degree Program	BSc in Electrical and Computer Engineering			
Module Title	Digital Electronics			
Pre-requisites	ECEg4132 (Computer Architecture and Organization)			
ECTS	5			
Contact Hours (per week)	Lecture	Tutorial	Laboratory	Home study
	2	1	2	5
Target Groups: <u>4th Year</u> Section: <u>Computer Eng.</u> Semester: <u>II</u> Academic Year: <u>2024</u>				
Assessment Methods	<ul style="list-style-type: none"> • Quiz (5%), Test (15%), Assignments/Project (15%), Laboratory exercise (15%) • Final exam (50%) 			
Course policies	<p>All students are expected to abide by the code of conduct of students throughout this course.</p> <ul style="list-style-type: none"> ✚ Academic dishonesty, including cheating, fabrication, and plagiarism will not be tolerated. ✚ Class activities will vary day to day, ranging from lectures to discussions. ✚ Students will be active participants in the course. ✚ Students are required to submit and present the assignments/projects provided according to the time table indicated. ✚ 100% of class attendance is mandatory! ✚ Every student should be on time for the session. Students are not allowed to enter if they are late more than five minutes. ✚ Active participation in the lab is essential. ✚ Cell phones MUST be turned off before entering the lab. 			

COURSE OBJECTIVES

- To understand MOS transistor fabrication processes.
- To understand basic circuit concepts.
- To have an exposure to the design rules to be followed for drawing the layout of circuits.
- Design of building blocks using different approaches.
- To have a knowledge of the testing processes of CMOS circuits.

CHAPTER I

Introduction: Brief Introduction to IC technology MOS, PMOS, NMOS, CMOS & BiCMOS Technologies Basic Electrical Properties of MOS and BiCMOS Circuits: $I_{DS} - V_{DS}$ relationships, MOS transistor Threshold Voltage- V_T , figure of merit μ_0 , Transconductance-gm, gds; Pass transistor, NMOS Inverter, Various pull ups, CMOS Inverter analysis and design, Bi-CMOS Inverters.

CHAPTER II

VLSI Circuit Design Processes: VLSI Design Flow, MOS Layers, Stick Diagrams, Design Rules and Layout, Lambda(λ)-based design rules for wires, contacts and Transistors, Layout Diagrams for NMOS and CMOS Inverters and Gates, Scaling of MOS circuits, Limitations of Scaling.

CHAPTER III

Gate level Design: Logic gates and other complex gates, Switch logic, Alternate gate circuits. Basic Circuit Concepts: Sheet Resistance R_s and its concepts to MOS, Area Capacitances calculations, Inverter Delays, Driving large Capacitive Loads, Wiring Capacitances, Fan-in and fan-out.

CHAPTER IV

Subsystem Design: Shifters, Adders, ALUs, Multipliers, Parity generators, Comparators, Counters. VLSI Design styles: Full-custom, Standard Cells, Gate-arrays, FPGAs, CPLDs and Design Approach for Full-custom and Semi-custom devices, parameters influencing low power design.

CHAPTER V

CMOS Testing: CMOS Testing, Need for Testing, Test Principles, Design Strategies for Test, Chip Level and Board Level Test Techniques.

REFERENCE BOOKS:

1. Essentials of VLSI Circuits and Systems, Kamran Eshraghian, Eshraghian Douglas, A.Pucknell, 2005, PHI.
2. Modern VLSI Design – Wayne Wolf, 3 Ed., 1997, Pearson Education.
3. CMOS VLSI Design-A Circuits and Systems Perspective, Neil H.E Weste, David Harris, Ayan Banerjee, 3rd Edn, Pearson, 2009.